

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

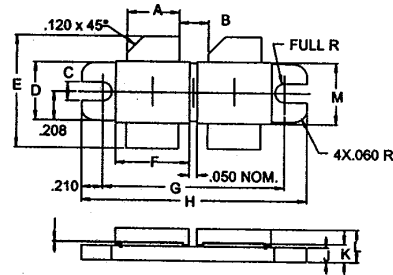
The **ASI SD1492-2** is a Common Emitter Device Designed for Class A and AB Amplifier Applications in Television Band IV & V Transmitters.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting
- Internal Matching

**MAXIMUM RATINGS**

$I_C$	25 A
$V_{CBO}$	60 V
$P_{DISS}$	300 W @ $T_C = 25^\circ\text{C}$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	0.55 °C/W

**PACKAGE STYLE .450 BAL FLG.(A)**


DIM	MINIMUM Inches / mm	MAXIMUM Inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.68	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L	.250 / 6.35	
M	.445 / 11.30	.457 / 11.61

**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS (PER SIDE)	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 100\text{ mA}$	30			V
$BV_{CBO}$	$I_C = 100\text{ mA}$	60			V
$BV_{EBO}$	$I_E = 50\text{ Ma}$	3.0			V
$I_{CES}$	$V_{CE} = 28\text{ V}$			10	mA
$h_{FE}$	$V_{CE} = 5.0\text{ V}$ $I_C = 3.0\text{ A}$	15		70	---
$C_{OB}$	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			100	pF
$P_{OUT}$	$V_{CE} = 28\text{ V}$ $I_{CQ} = 2 \times 500\text{ mA}$ $f = 860\text{ MHz}$	150			W
$G_P$	$V_{CE} = 28\text{ V}$ $I_{CQ} = 2 \times 250\text{ mA}$ $f = 860\text{ MHz}$ $P_{out} = 50\text{ W}$	6.5			dB
$\eta_c$	$V_{CE} = 26.5\text{ V}$ $P_{out} = 25\text{ W}$ $f = 860\text{ MHz}$ VISION = -8.0dB      SOUND = -10 dB      CHROMA = -16dB			-45	dBc